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Quad. 2-input NAND Schmitt Triggers

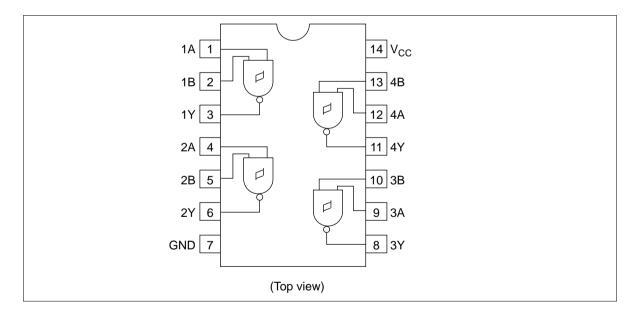
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ADE-205-441 (Z) 1st. Edition Sep. 2000

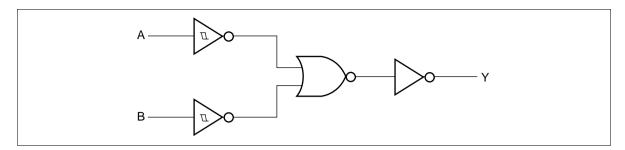
Features

- High Speed Operation: $t_{pd} = 9.5$ ns typ ($C_L = 50$ pF)
- High Output Current: Fanout of 10 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 2 \text{ to } 6 \text{ V}$
- Low Input Current: 1 µA max
- Low Quiescent Supply Current: I_{CC} (static) = 1 μ A max (Ta = 25°C)

Pin Arrangement



Logic Diagram (1/4)



DC Characteristics

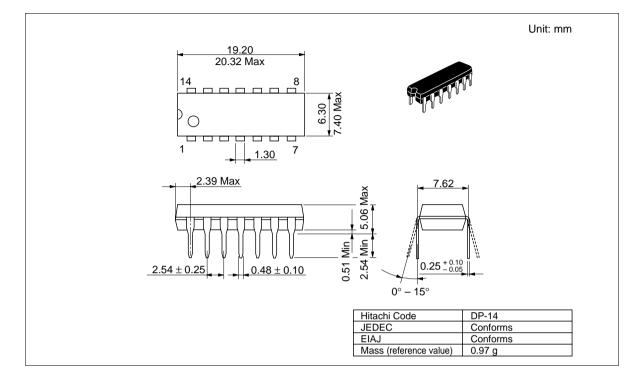
| | | | Ta = | 25°C | ; | Ta = - +85°C | -40 to | | | |
|--------------------------|-----------------|---------------------|------|------|------|-----------------|--------|------|---|----|
| Item | Symbol | V _{cc} (V) | Min | Тур | Max | Min | Max | Unit | Test Conditions | |
| Threshold voltage | V_{T+} | 2.0 | 0.8 | — | 1.5 | 0.8 | 1.5 | V | | |
| | | 4.5 | 2.25 | — | 3.15 | 2.25 | 3.15 | _ | | |
| | | 6.0 | 3.0 | — | 4.2 | 3.0 | 4.2 | | | |
| | V_{T-} | 2.0 | 0.2 | — | 1.0 | 0.2 | 1.0 | V | | |
| | | 4.5 | 0.9 | — | 2.25 | 0.9 | 2.25 | | | |
| | | 6.0 | 1.2 | — | 3.0 | 1.2 | 3.0 | _ | | |
| Hysteresis voltage | V _H | 2.0 | 0.2 | — | 1.2 | 0.2 | 1.2 | V | | |
| | | 4.5 | 0.4 | _ | 2.25 | 0.4 | 2.25 | _ | | |
| | | 6.0 | 0.6 | — | 3.0 | 0.6 | 3.0 | _ | | |
| Output voltage | V _{OH} | 2.0 | 1.9 | 2.0 | — | 1.9 | — | V | Vin = V _{IH} or V _{IL} $I_{OH} = -20 \ \mu A$ | ł |
| | | 4.5 | 4.4 | 4.5 | _ | 4.4 | _ | _ | | |
| | | 6.0 | 5.9 | 6.0 | | 5.9 | — | - | | |
| | | 4.5 | 4.18 | _ | _ | 4.13 | _ | _ | $I_{OH} = -4 \text{ mA}$ $I_{OH} = -5.2 \text{ m}$ | |
| | | 6.0 | 5.68 | | | 5.63 | _ | - | I _{он} = -5.2 m | ۱A |
| | V _{OL} | 2.0 | _ | 0.0 | 0.1 | — | 0.1 | V | Vin = V _{IH} or V _{IL} I_{OL} = 20 μ A | |
| | | 4.5 | _ | 0.0 | 0.1 | — | 0.1 | | | |
| | | 6.0 | | 0.0 | 0.1 | — | 0.1 | - | | |
| | | 4.5 | | | 0.26 | | 0.33 | = | $I_{OL} = 4 \text{ mA}$ | |
| | | 6.0 | | _ | 0.26 | _ | 0.33 | _ | $I_{OL} = 5.2 \text{ mA}$ | 1 |
| Input current | lin | 6.0 | _ | _ | ±0.1 | _ | ±1.0 | μA | $Vin = V_{cc} \text{ or } GND$ | |
| Quiescent supply current | I _{cc} | 6.0 | — | | 1.0 | _ | 10 | μA | Vin = V_{cc} or GND, lout = 0 μ | ιA |

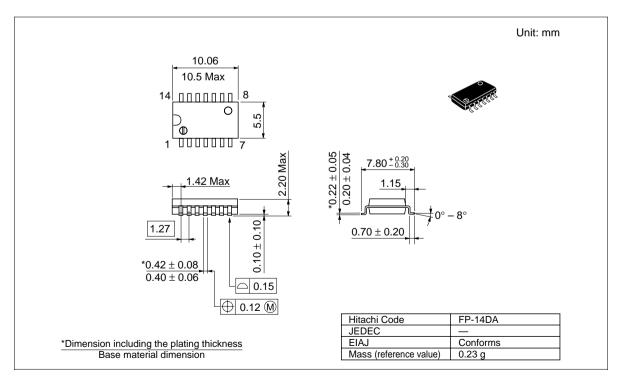
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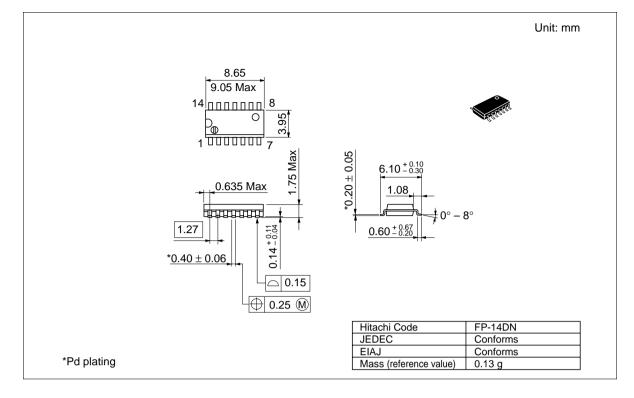
| | | | Ta = 25°C | | Ta = –40 to +85°C | | | | |
|-------------------|------------------|--------------|-----------|-----|----------------------|-----|-----|------|-----------------|
| Item | Symbol | V_{cc} (V) | Min | Тур | Max | Min | Max | Unit | Test Conditions |
| Propagation delay | t _{PLH} | 2.0 | _ | _ | 100 | _ | 125 | ns | |
| time | | 4.5 | | 8 | 20 | — | 25 | | |
| | | 6.0 | | — | 17 | — | 21 | _ | |
| | t _{PHL} | 2.0 | | _ | 100 | — | 125 | ns | |
| | | 4.5 | | 11 | 20 | — | 25 | _ | |
| | | 6.0 | | _ | 17 | — | 21 | _ | |
| Output rise/fall | t _{TLH} | 2.0 | | _ | 75 | — | 95 | ns | |
| time | t _{THL} | 4.5 | | 5 | 15 | — | 19 | _ | |
| | | 6.0 | | _ | 13 | — | 16 | _ | |
| Input capacitance | Cin | | | 5 | 10 | | 10 | pF | |

AC Characteristics ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

Package Dimensions







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